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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.	
10/681,346	10/09/2003	Soo-Doo Chae	249/286 DIV.	8321	
7:	590 07/01/2004	EXAMINER			
LEE & STERBA, P.C.			LE, DUNG ANH		
SUITE 2000			ART UNIT	PAPER NUMBER	
1101 WILSON BOULEVARD ARLINGTON, VA 22209			2818	TALLANDIN	
			2010		
			DATE MAILED: 07/01/2004		

Please find below and/or attached an Office communication concerning this application or proceeding.

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		Application No.	Ap	oplicant(s)				
		10/681,346	CH	HAE ET AL.				
	Office Action Summary	Examin r	Ar	t Unit				
		DUNG A LE	28	18				
Period fo	Th MAILING DATE of this communication or Reply	appears on the cov	r sheet with the corre	spondenc address	} 			
A SHO THE N - Exten after: - If the - If NO - Failur Any re	ORTENED STATUTORY PERIOD FOR REMAILING DATE OF THIS COMMUNICATION IS SIGNED TO STATUTORY PERIOD FOR REMAILING DATE OF THIS COMMUNICATION IS SIX (6) MONTHS from the mailing date of this communication. Period for reply specified above is less than thirty (30) days, a period for reply is specified above, the maximum statutory per reto reply within the set or extended period for reply will, by state to reply within the set or extended period for reply will, by state ply received by the Office later than three months after the main displacement. See 37 CFR 1.704(b).	N. 1.136(a). In no event, howeverther within the statutory minding will apply and will expire atute, cause the application to	ever, may a reply be timely fil nimum of thirty (30) days will SIX (6) MONTHS from the m o become ABANDONED (35	iled be considered timely. nailing date of this communi 5 U.S.C. § 133).	ication.			
Status								
1)	Responsive to communication(s) filed on							
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Dispositi	on of Claims							
5)□ 6)□ 7)⊠	Claim(s) <u>24-53</u> is/are pending in the applica 4a) Of the above claim(s) is/are without Claim(s) is/are allowed. Claim(s) is/are rejected. Claim(s) <u>24-53</u> is/are objected to. Claim(s) are subject to restriction and	drawn from consider						
Applicati	on Papers							
10) 🖾 -	The specification is objected to by the Examember The drawing(s) filed on <u>9 October 2003</u> is/and Applicant may not request that any objection to the Replacement drawing sheet(s) including the contract of the oath or declaration is objected to by the	re: a)⊠ accepted o the drawing(s) be held rection is required if th	in abeyance. See 37 e drawing(s) is objecte	CFR 1.85(a). ed to. See 37 CFR 1.1				
Priority u	ınder 35 U.S.C. § 119							
12) <u> </u>	Acknowledgment is made of a claim for fore All b) Some * c) None of: 1. Certified copies of the priority documents. Certified copies of the priority documents. Copies of the certified copies of the papplication from the International Burstee the attached detailed Office action for a	ents have been rece ents have been rece priority documents have reau (PCT Rule 17.2	eived. eived in Application Nave been received in E(a)).	No	e			
	t(s) e of References Cited (PTO-892) e of Draftsperson's Patent Drawing Review (PTO-948)	4) 🗆	Interview Summary (PTC Paper No(s)/Mail Date		Ne -			
3) 🛛 Inform	e of Draftsperson's Patent Drawing Review (PTO-948) nation Disclosure Statement(s) (PTO-1449 or PTO/SB/ r No(s)/Mail Date <u>4/1/2004</u> .		Notice of Informal Paten Other:					

DETAIL ACTION

Response to Preliminary Amendment

In Preliminary Amendment, applicant cancels claims 1- 23, and 24- 53 are remained for examination is acknowledged.

Priority

Acknowledge is made of applicants' claim for foreign priority base on an application 2001-25569 filed in Republic of Korea on 5/10/2001.

It is noted that Applicants have filled a certified copy of said application as required by U.S.C 119, which papers have been placed of record in the file.

Oath/Declaration

The oath/declaration filed on 10/09/2003 is acceptable.

Information Disclosure Statement

This office acknowledges of the following items from the Applicant:

Information Disclosure Statement (IDS) filed on 4/1/2004 and made of record.

The references cited on the PTOL 1449 form have been considered.

This application is in condition for allowance except for the following formal matters:

The specification is objected to for the following reasons:

- 1) The title of the invention is not descriptive. A new title is required that is clearly indicative of the invention to which the claims are directed (see MPEP § 606.01).
- 2) A new abstract is required that is clearly indicative the invention to which the claims are directed.

Note that, the claims are directed to a method of making a semiconductor device instead of to a semiconductor device.

The specification has been checked to the extent necessary to determine the presence of all possible minor errors. However, the applicant's cooperation is requested in correcting any errors of which applicant may become aware in the specification.

Reasons for Indication of Allowable Subject Matter

Claims 1-20 would be allowed. The following is an examiner's statement of reason for allowance:

Set of claims 24- 29: none of the references of record teaches or suggests the claimed Method for manufacturing a single electron memory device including a single electron storage element in a gate lamination pattern formed on a nano-scale channel region of a MOSFET, wherein formation of the gate lamination pattern having

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the step of forming s lower layer and a single electron storage medium for storing a single electron tunneling through the lower layer on a substrate and among other steps/limitations as cited in independent claim 24.

Set of claims 33-41: none of the references of record teaches or suggests the claimed Method for manufacturing a single electron memory device including a single electron storage element in a gate lamination pattern formed on a nano-scale channel region of a MOSFET, wherein formation of the gate lamination pattern having the step of forming a upper layer including a plurality of vertically spaced-apart first and second quantum dots on the lower layer and among other steps/limitations as cited in independent claim 33.

Set of claims 42-53: none of the references of record teaches or suggests the claimed Method for manufacturing a single electron memory device including a single electron storage element in a gate lamination pattern formed on a nano-scale channel region of a MOSFET, wherein formation of the gate lamination pattern having the step of forming sequentially forming a single electron storage means for storing a single electron tunneling through the lower layer, and an upper layer covering the single electron storage means, on the lower layer, wherein the surface of the upper layer is uneven and among other steps/limitations as cited in independent claim 42.

Prosecution on the merits is closed in accordance with the practice under *Ex parte*Ouayle, 1935 C.D. 11, 453 O.G. 213.

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A shortened statutory period for reply to this action is set to expire TWO MONTHS from the mailing date of this letter.

When responding to the office action, Applicants' are advice to provide the examiner with the line numbers and page numbers in the application and/or references cited to assist the examiner to locate the appropriate paragraphs.

Conclusion

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Dung A. Le whose telephone number is (571) 272-1784. The examiner can normally be reached on Monday-Friday 8:00am-5: 30pm.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, David Nelms can be reached on (571) 272-1787. The fax phone numbers for the organization where this application or proceeding is assigned are (703) 872-9306 for regular communications and (703) 872-9306 for After Final communications.

Any inquiry of a general nature or relating to the status of this application or proceeding should be directed to the receptionist whose telephone number is (703) 308-0956.

Dung A. Le

P. Examiner.